CBCS SCHEME

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TION						West No. 7	18EC33
USN							

Third Semester B.E. Degree Examination, Aug./Sept.2020 **Electronic Devices**

Max. Marks: 100 Time 3 hrs

Tir	ne: í	3 hrs. Max. Mark	s: 100
	Λ	Note: Answer any FIVE full questions, choosing ONE full question from each module	e.
1	a. b.) Marks)) Marks)
		OR C	
2	a. b.	What is Hall-effect? With suitable diagram and equation explain how does Hall	Marks) ll-effect Marks)
		Module-2	
3	a. b.	What is tunneling? Explain voltage current characteristic of a tunnel diode with the energy band diagram. Mention the differences between Zener effect and Avalanche effect. (03	help of Marks) Marks) Marks)
	C.	Explain light emitting diode with a heat sketch.	(Walks)
		OR OF	
4	a.	Explain qualitative description of current flow at forward and reverse bias junction diode. (10	on of a Marks)
	b.		
			Marks)
		Module-3	
5	a.		Marks)
	b.	Draw the Ebers – Moll model for a PNP transistor and explain its significance. (10) Marks)
		OR	
6	a.		Marks)
U			Marks)
			Marks)
		. Module-4	
7	a.	Explain the construction and operation of n-JFET with neat diagram and equations.	
	1-		Marks)
		Explain the principle of operation n-channel enhancement mode MOSFET wir	Marks)
	c.		Marks)
	,	diagram and equations.	,
		OR	
8	a.	Explain two-terminal MOS structure using energy band diagram. (10	Marks)
	b.	Explain the principle of operation of p-channel enhancement mode MOSFET wi	ith neat
		diagram and equations. (10	Marks)
		1 of 2	

Module-5
Explain thermal oxidation process with neat diagram. (10 Marks)

What is metallization process explain with neat diagram by showing all the steps in the (10 Marks) fabrication of p-n junctions.

OR

a. Explain integration of other circuit elements with suitable diagrams.b. Explain CMOS process of integration with the help of neat diagram. (10 Marks)

(10 Marks)